



## SOD-323 Plastic-Encapsulate Diode

### B5817WS SCHOTTKY BARRIER DIODE

#### FEATURES

Power dissipation

$P_D$ : 200 mW ( $T_{amb}=25^\circ\text{C}$ )

Collector current

$I_F$ : 1 A

Collector-base voltage

$V_R$ : 20 V

Operating and storage junction temperature range

$T_J, T_{stg}$ :  $-55^\circ\text{C}$  to  $+150^\circ\text{C}$



MARKING: SJ

#### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=1\text{mA}$	20		V
Reverse voltage leakage current	$I_R$	$V_R=20\text{V}$		1	mA
Forward voltage	$V_F$	$I_F=1\text{A}$ $I_F=3\text{A}$		0.45 0.75	V
Diode capacitance	$C_D$	$V_R=4\text{V}, f=1\text{MHz}$		120	pF